

SOT-523 Bias Resistor Transistor NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors: a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The device is designed for low power surface mount applications.

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	nbol Parameter		Units	
V _{сво}	Collector-Base Voltage	50	V	
V _{CEO}	Collector-Emitter Voltage	50	V	
Ιc	Collector Current	100	mA	
PD	Power Dissipation	150	mW	
R _{0JA}	Thermal Resistance from Junction to Ambient	600	°C /W	
T _J T _{STG}	Junction & Storage Temperature Range	-55 to +150	°C	





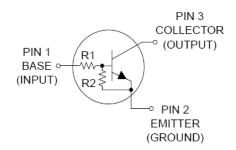
SOT-523 (SC-75A)

These ratings are limiting values above which the serviceability of the device may be impaired.

Specification Features:

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

Electrical Symbol:





e Marking & Resistor Values:					
Device	Marking	R1 (KΩ)	R2 (KΩ)		
DTC114EE	24	10	10		
DTC124EE	25	22	22		
DTC144EE	26	47	47		
DTC114YE	64	10	47		
DTC114TE	04	10	∞		
DTC143TE	03	4.7	∞		
DTC123EE	22	2.2	2.2		
DTC143EE	23	4.7	4.7		
DTC143ZE	E23	4.7	47		
DTC124XE	45	22	47		
DTC123JE	E42	2.2	47		

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Off Characteristics

Symbol	Parameter	Test Condition	Limits			Unit
Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
I _{сво}	Collector-Base Cutoff Current	V _{CB} =50V, I _E =0A	-	-	100	nA
ICEO	Collector-Emitter Cutoff Current	V _{CE} =50V, I _B =0A	-	-	500	nA
I _{EBO}	Emitter-Base Cutoff Current	V _{EB} =6.0V, I _C =0A				
	DTC114EE		-	-	0.50	
	DTC124EE		-	-	0.20	
	DTC144EE		-	-	0.10	
	DTC114YE		-	-	0.20	
	DTC114TE		-	-	0.90	mA
	DTC143TE		-	-	1.90	IIIA
	DTC123EE		-	-	2.30	
	DTC143EE		-	-	1.50	
	DTC143ZE		-	-	0.18	
	DTC124XE		-	-	0.13	
	DTC123JE		-	-	0.20	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C =10uA, I _E =0A	50	-	-	Volts
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage (Note 1)	I _C =2.0mAA, I _B =0A	50	-	-	Volts

Note 1: Pulse Test. Pulse width <300us, Duty cycle < 2.0%)



Sumahal	Devemeter	Test Condition	Limits			11
Symbol	Parameter		Min	Тур	Мах	Unit
H _{FE}	DC Current Dain	V_{CE} =10V, I_{C} =5.0mA				
	DTC114EE		35	60		
	DTC124EE		60	100		
	DTC144EE		80	140		
	DTC114YE		80	140		
	DTC114TE		160	350		
	DTC143TE		160	350		
	DTC123EE		8.0	15		
	DTC143EE		15	30		
	DTC143ZE		80	200		
	DTC124XE		80	150		
	DTC123JE		80	140		
V _{CE(sat)}	Collector-Emitter Saturation Voltage					
	DTC114EE	I _C =10mA, I _B =0.3mA				
	DTC124EE	I _C =10mA, I _B =0.3mA				
	DTC144EE	I _C =10mA, I _B =0.3mA				
	DTC114YE	I _C =10mA, I _B =0.3mA				
	DTC114TE	I _C =10mA, I _B =1mA			0.05	Val
	DTC143TE	I _C =10mA, I _B =1mA			0.25	Vol
	DTC123EE	I _C =10mA, I _D =5mA				
	DTC143EE	I_{C} =10mA, I_{D} =1mA				
	DTC143ZE	I _C =10mA, I _D =1mA				
	DTC124XE	I_{C} =10mA, I_{B} =1mA				
	DTC123JE	I_{C} =10mA, I_{B} =0.3mA				
V _{OL}	Output Voltage (on)	R _L = 1.0KΩ				
	DTC114EE	V_{CC} =5.0V, V_{B} =2.5V				
	DTC124EE	V_{CC} =5.0V, V_{B} =2.5V				
	DTC144EE	V_{CC} =5.0V, V_{B} =3.5V				
	DTC114YE	V_{CC} =5.0V, V_{B} =2.5V				
	DTC114TE	V_{CC} =5.0V, V_{B} =2.5V			0.00	Val
	DTC143TE	V_{CC} =5.0V, V_{B} =2.5V			0.20	Vol
	DTC123EE	V_{CC} =5.0V, V_{B} =2.5V				
	DTC143EE	V_{CC} =5.0V, V_{B} =2.5V				
	DTC143ZE	V _{CC} =5.0V, V _B =2.5V				
	DTC124XE	V_{CC} =5.0V, V_{B} =2.5V				
	DTC123JE	V _{CC} =5.0V, V _B =2.5V				



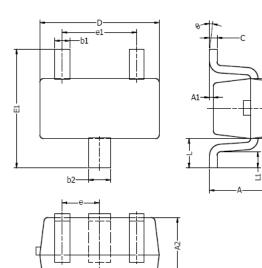
Symbol	Demonster	To at Canditian		Limits		
	Parameter	Test Condition	Min	Тур	Max	Unit
V _{он}	Output Voltage (on)	R _L = 1.0KΩ				
	DTC114	E V _{CC} =5.0V, V _B =0.5V				
	DTC124	EE V _{CC} =5.0V, V _B =0.5V				
	DTC144	E V _{CC} =5.0V, V _B =0.5V				
	DTC114	YE V _{CC} =5.0V, V _B =0.5V				Volts
	DTC114	E V _{CC} =5.0V, V _B =0.25V	4.9			
	DTC143	TE V _{CC} =5.0V, V _B =0.25V	4.9			
	DTC123	E V _{CC} =5.0V, V _B =0.5V				
	DTC143	EE V _{CC} =5.0V, V _B =0.5V				
	DTC1432	ZE V _{CC} =5.0V, V _B =0.25V				
	DTC124X	KE V _{CC} =5.0V, V _B =0.5V				
	DTC123	IE V _{CC} =5.0V, V _B =0.5V				

Electrical Characteristics (T_A = 25°C unless otherwise noted)

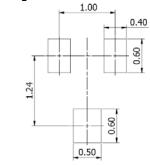
Symbol	Charac	teristic	Min	Тур	Мах	Unit
R1	Input Resistor	DTC114EE	7.0	10	13	
		DTC124EE	15.4	22	28.6	
		DTC144EE	32.9	47	61.1	
		DTC114YE	7.0	10	13	
		DTC114TE	7.0	10	13	
		DTC143TE	3.3	4.7	6.1	ΚΩ
		DTC123EE	1.5	2.2	2.9	
		DTC143EE	3.3	4.7	6.1	
		DTC143ZE	3.3	4.7	6.1	
		DTC124XE	15.4	22	28.6	
		DTC123JE	1.54	2.2	2.86	
R1/R2	Resistor Ratio	DTC114EE	0.8	1.0	1.2	
		DTC124EE	0.8	1.0	1.2	
		DTC144EE	0.8	1.0	1.2	
		DTC114YE	0.17	0.21	0.25	
		DTC114TE	-	-	-	
		DTC143TE	-	-	-	
		DTC123EE	0.8	1.0	1.2	
		DTC143EE	0.8	1.0	1.2	
		DTC143ZE	0.055	0.1	0.185	
		DTC124XE	0.38	0.47	0.56	
		DTC123JE	0.038	0.047	0.056	



SOT-523 Package Outline



Typical Soldering Pattern:



DIM	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
А	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
С	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
е	0.50	TYP.	0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016	REF.
L1	0.10	0.30	0.004	0.012
θ	0 °	8 °	0 °	8 °

NOTES:

1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.

2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.



NOTICE

The information presented in this document is for reference only. Tak Cheong reserves the right to make changes without notice for the specification of the products displayed herein.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Tak Cheong Semiconductor Co., Ltd., or anyone on its behalf, assumes no responsibility or liability for any damagers resulting from such improper use of sale.

This publication supersedes & replaces all information reviously supplied. For additional information, please visit our website <u>http://www.takcheong.com</u>, or consult your nearest Tak Cheong's sales office for further assistance.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - Pre-Biased category:

Click to view products by Tak Cheong manufacturer:

Other Similar products are found below :

RN1607(TE85L,F) DRC9A14E0L DTA124GKAT146 DTA144WETL DTA144WKAT146 DTC113EET1G DTC115TETL DTC115TKAT146 DTC124TETL DTC144VUAT106 MUN5241T1G BCR158WH6327XTSA1 NSBA114TDP6T5G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F) RN1306(TE85L,F) RN4605(TE85L,F) TTEPROTOTYPE79 EMH15T2R SMUN2214T3G SMUN5335DW1T1G NSBC143ZPDP6T5G NSVMUN5113DW1T3G SMUN5230DW1T1G SMUN2214T1G FMA7AT148 DTC114EUA-TP NSVDTA114EET1G SMUN5237DW1T1G SMUN5213DW1T1G SMUN5114DW1T1G SMUN2111T1G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G NSVDTC143ZM3T5G SMUN5335DW1T2G SMUN5216DW1T1G NSVMUN5316DW1T1G NSVMUN5215DW1T1G NSVMUN5213DW1T3G NSVMUN2112T1G NSVIMD10AMT1G NSVEMC2DXV5T1G NSVDTC144WET1G